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TL082 Wide Bandwidth Dual JFET Input Operational Amplifier

Check for Samples: TL082-N

FEATURES

Internally Trimmed Offset Voltage: 15 mV

Low Input Bias Current: 50 pA

Low Input Noise Voltage: 16nV/√Hz

• Low Input Noise Current: 0.01 pA/√Hz

· Wide Gain Bandwidth: 4 MHz

High Slew Rate: 13 V/µs

• Low Supply Current: 3.6 mA

• High Input Impedance: 10¹²Ω

Low Total Harmonic Distortion: ≤0.02%

Low 1/f Noise Corner: 50 Hz

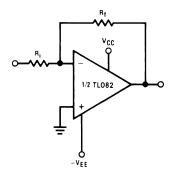
Fast Settling Time to 0.01%: 2 µs

DESCRIPTION

These devices are low cost, high speed, dual JFET input operational amplifiers with an internally trimmed input offset voltage (BI-FET II™ technology). They require low supply current yet maintain a large gain bandwidth product and fast slew rate. In addition, well matched high voltage JFET input devices provide very low input bias and offset currents. The TL082 is pin compatible with the standard LM1558 allowing designers to immediately upgrade the overall performance of existing LM1558 and most LM358 designs.

These amplifiers may be used in applications such as high speed integrators, fast D/A converters, sample and hold circuits and many other circuits requiring low input offset voltage, low input bias current, high input impedance, high slew rate and wide bandwidth. The devices also exhibit low noise and offset voltage drift.

Typical Connection



Connection Diagram

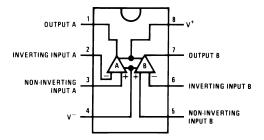


Figure 1. PDIP/SOIC Package (Top View) See Package Number D0008A or P0008E

M

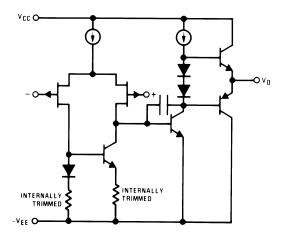
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BI-FET II is a trademark of dcl_owner.

All other trademarks are the property of their respective owners.



Simplified Schematic





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings (1)(2)

Supply Voltage	±18V
Power Dissipation (3)	(4)
Operating Temperature Range	0°C to +70°C
$T_{j(MAX)}$	150°C
Differential Input Voltage	±30V
Input Voltage Range (5)	±15V
Output Short Circuit Duration	Continuous
Storage Temperature Range	-65°C to +150°C
Lead Temp. (Soldering, 10 seconds)	260°C
ESD rating to be determined.	

- (1) "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits.
- (2) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.
- (3) The power dissipation limit, however, cannot be exceeded.
- (4) For operating at elevated temperature, the device must be derated based on a thermal resistance of 115°C/W junction to ambient for the P0008E package.
- (5) Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage.

DC Electrical Characteristics (1)

Comple ed	Donomotor.	Con ditions		11-16-		
Symbol	Parameter	Conditions	Min	Тур	Max	Units
Vos	Input Offset Voltage	$R_S = 10 \text{ k}\Omega, T_A = 25^{\circ}\text{C}$		5	15	mV
		Over Temperature			20	mV
$\Delta V_{OS}/\Delta T$	Average TC of Input Offset Voltage	$R_S = 10 \text{ k}\Omega$		10		μV/°C
I _{OS}	Input Offset Current	$T_j = 25^{\circ}C, (1)(2)$		25	200	pA
		T _j ≤ 70°C			4	nA
I _B	Input Bias Current	$T_j = 25^{\circ}C, (1)(2)$		50	400	pA
		T _j ≤ 70°C			8	nA
R _{IN}	Input Resistance	T _i = 25°C		10 ¹²		Ω

(1) These specifications apply for $V_S = \pm 15V$ and $0^{\circ}C \le T_A \le +70^{\circ}C$. V_{OS} , I_B and I_{OS} are measured at $V_{CM} = 0$.

(2) The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature, T_j. Due to the limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, P_D. T_j = T_A + θ_{jA} P_D where θ_{jA} is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.



DC Electrical Characteristics (1) (continued)

Compleal	Donomotor	Conditions		TL082C				
Symbol	Parameter	Conditions	Min	Тур	Max	Units		
A _{VOL}	Large Signal Voltage Gain	$V_S = \pm 15V, T_A = 25^{\circ}C, V_O = \pm 10V, R_L = 2 k\Omega$	25	100		V/mV		
		Over Temperature	15			V/mV		
Vo	Output Voltage Swing	$V_S = \pm 15V$, $R_L = 10 \text{ k}\Omega$	±12	±13.5		V		
V_{CM}	Input Common-Mode Voltage	$V_S = \pm 15V$	±11	+15		V		
	Range			-12		V		
CMRR	Common-Mode Rejection Ratio	$R_S \le 10 \text{ k}\Omega$	70	100		dB		
PSRR	Supply Voltage Rejection Ratio	(3)	70	100		dB		
I _S	Supply Current			3.6	5.6	mA		

⁽³⁾ Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously in accordance with common practice. $V_S = \pm 6V$ to $\pm 15V$.

AC Electrical Characteristics (1)

Cumbal	Donomotor.	Conditions		Unita		
Symbol	Parameter	Conditions	Min	Тур	Max	Units
	Amplifier to Amplifier Coupling	T _A = 25°C, f = 1Hz-20 kHz (Input Referred)		-120		dB
SR	Slew Rate	$V_S = \pm 15V, T_A = 25^{\circ}C$	8	13		V/µs
GBW	Gain Bandwidth Product	$V_S = \pm 15V, T_A = 25^{\circ}C$		4		MHz
e _n	Equivalent Input Noise Voltage	$T_A = 25^{\circ}C$, $R_S = 100\Omega$, $f = 1000 \text{ Hz}$		25		nV/√Hz
i _n	Equivalent Input Noise Current	$T_j = 25$ °C, $f = 1000 \text{ Hz}$		0.01		pA/√Hz
THD	Total Harmonic Distortion	$A_V = +10$, $R_L = 10k$, $V_O = 20 \ Vp - p$, $BW = 20 \ Hz - 20 \ kHz$		<0.02		%

⁽¹⁾ These specifications apply for $V_S = \pm 15 V$ and $0^{\circ}C \leq T_A \leq +70^{\circ}C$. V_{OS} , I_B and I_{OS} are measured at $V_{CM} = 0$.

Product Folder Links: TL082-N



Typical Performance Characteristics

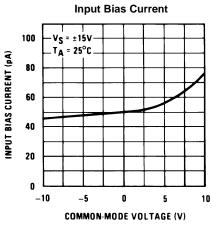
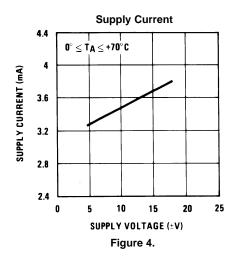


Figure 2.



Negative Common-Mode Input Voltage Limit 20 0°C \leq TA \leq +70°C | 15 15 10 15 20 NEGATIVE SUPPLY VOLTAGE (V) Figure 6.

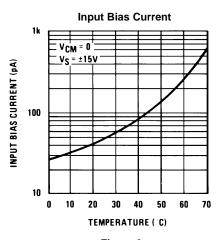


Figure 3.

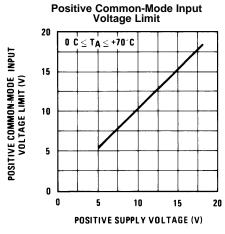
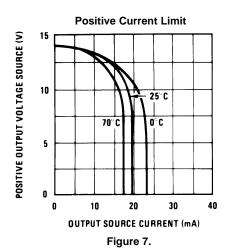


Figure 5.





Typical Performance Characteristics (continued)

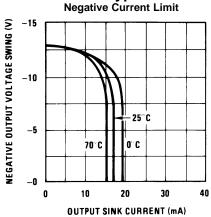


Figure 8.

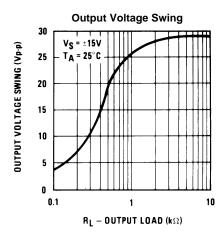
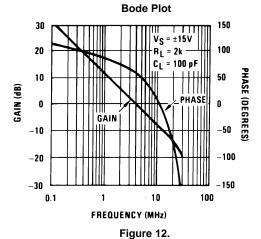


Figure 10.



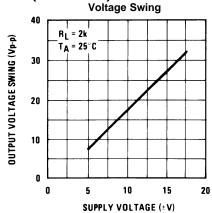
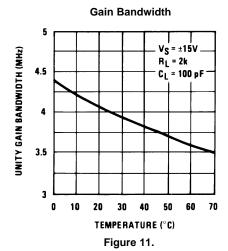


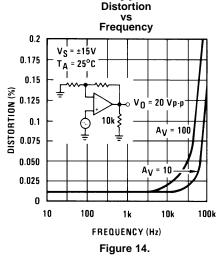
Figure 9.

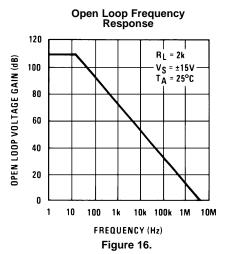


Slew Rate 15 V_S = ±15V R_ = 2k $A_V = 1$ FALLING 14 SLEW RATE (V/µs) 13 RISING 12 11 10 20 30 40 TEMPERATURE (°C) Figure 13.



Typical Performance Characteristics (continued)





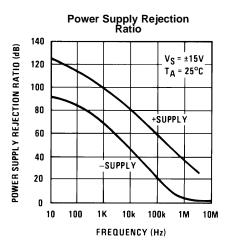
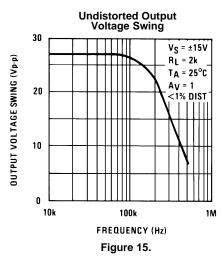
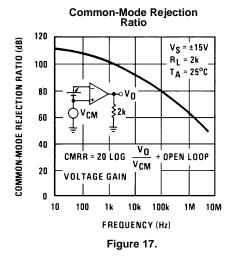
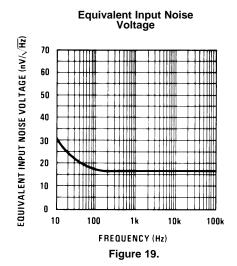


Figure 18.

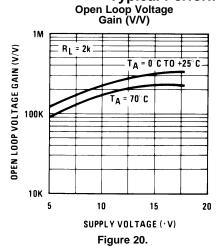


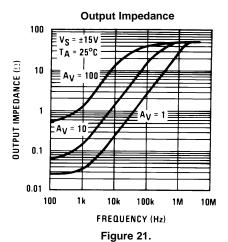


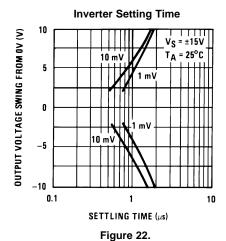




Typical Performance Characteristics (continued)



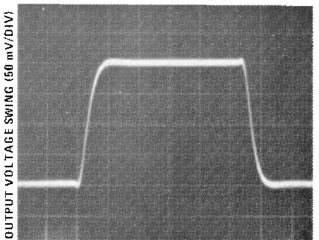






Pulse Response

Small Signal Inverting



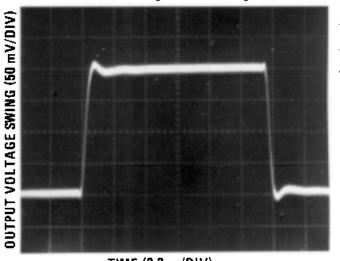
TIME (0.2 µs/DŧV) Figure 23.

OUTPUT VOLTAGE SWING (5V/DIV)

Large Signal Inverting

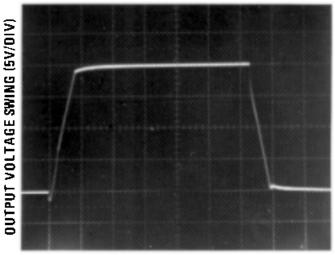
TIME (2 µs/DIV)
Figure 24.

Small Signal Non-Inverting



TIME (0.2 μ s/DIV) Figure 25.

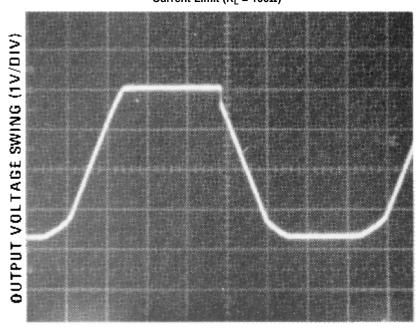
Large Signal Non-Inverting



TIME (2 μs/DIV)
Figure 26.



Pulse Response (continued) Current Limit ($R_L = 100\Omega$)



TIME (5 $\mu s/DIV$)

Figure 27.

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APPLICATION HINTS

These devices are op amps with an internally trimmed input offset voltage and JFET input devices (BI-FET II). These JFETs have large reverse breakdown voltages from gate to source and drain eliminating the need for clamps across the inputs. Therefore, large differential input voltages can easily be accommodated without a large increase in input current. The maximum differential input voltage is independent of the supply voltages. However, neither of the input voltages should be allowed to exceed the negative supply as this will cause large currents to flow which can result in a destroyed unit.

Exceeding the negative common-mode limit on either input will cause a reversal of the phase to the output and force the amplifier output to the corresponding high or low state. Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output; however, if both inputs exceed the limit, the output of the amplifier will be forced to a high state.

The amplifiers will operate with a common-mode input voltage equal to the positive supply; however, the gain bandwidth and slew rate may be decreased in this condition. When the negative common-mode voltage swings to within 3V of the negative supply, an increase in input offset voltage may occur.

Each amplifier is individually biased by a zener reference which allows normal circuit operation on ±6V power supplies. Supply voltages less than these may result in lower gain bandwidth and slew rate.

The amplifiers will drive a 2 k Ω load resistance to ±10V over the full temperature range of 0°C to +70°C. If the amplifier is forced to drive heavier load currents, however, an increase in input offset voltage may occur on the negative voltage swing and finally reach an active current limit on both positive and negative swings.

Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

Because these amplifiers are JFET rather than MOSFET input op amps they do not require special handling.

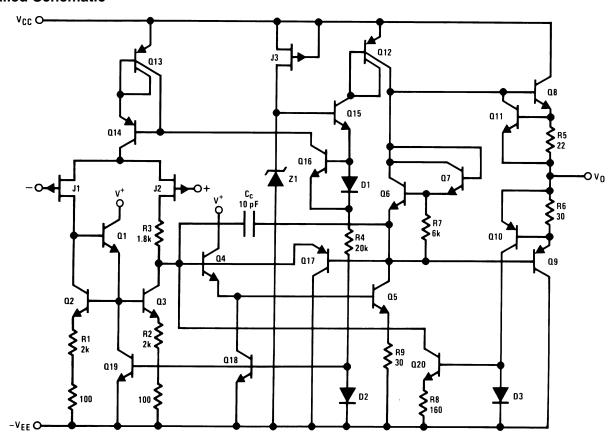
As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pick-up" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3 dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately 6 times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.

Product Folder Links: TL082-N

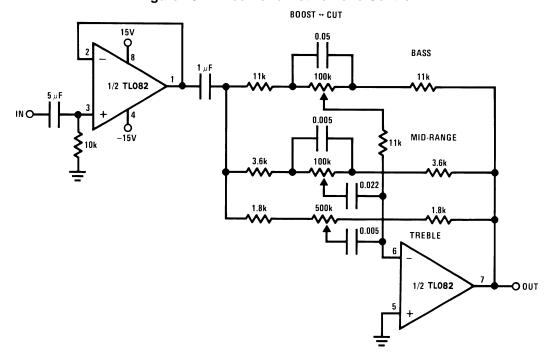


Detailed Schematic



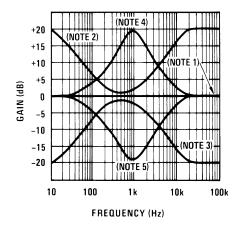
Typical Applications

Figure 28. Three-Band Active Tone Control



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- All potentiometers are linear taper
- Use the LF347 Quad for stereo applications

All controls flat.

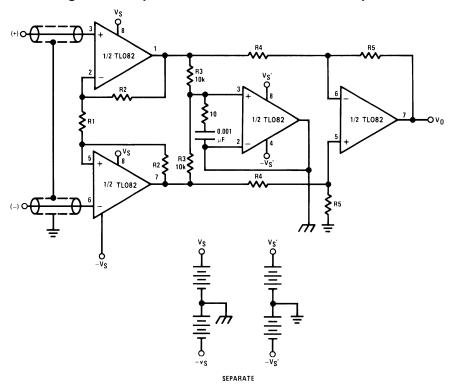
Bass and treble boost, mid flat.

Bass and treble cut, mid flat.

Mid boost, bass and treble flat.

Mid cut, bass and treble flat.

Figure 29. Improved CMRR Instrumentation Amplifier





$$A_V = \left(\frac{2R2}{R1} + 1\right) \frac{R5}{R4}$$

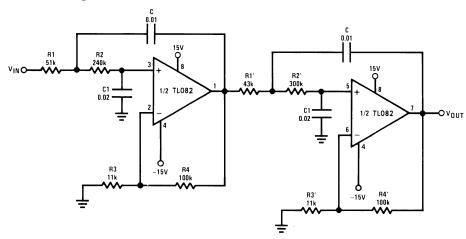
and are separate isolated grounds

Matching of R2's, R4's and R5's control CMRR

With A_{VT} = 1400, resistor matching = 0.01%: CMRR = 136 dB

- Very high input impedance
- Super high CMRR

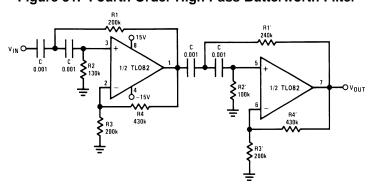
Figure 30. Fourth Order Low Pass Butterworth Filter



• Corner frequency (f_c) =
$$\sqrt{\frac{1}{\text{R1R2CC1}}} \cdot \frac{1}{2\pi} = \sqrt{\frac{1}{\text{R1'R2'CC1}}} \cdot \frac{1}{2\pi}$$

- Passband gain (H_0) = (1 + R4/R3) (1 + R4'/R3')
- First stage Q = 1.31
- Second stage Q = 0.541
- Circuit shown uses nearest 5% tolerance resistor values for a filter with a corner frequency of 100 Hz and a passband gain of 100
- Offset nulling necessary for accurate DC performance

Figure 31. Fourth Order High Pass Butterworth Filter



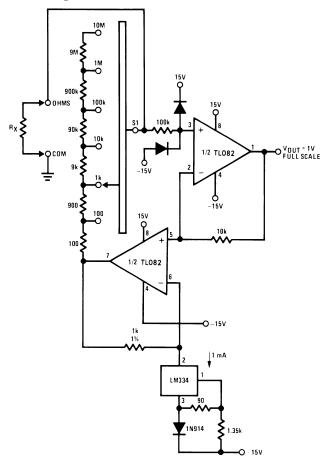
• Corner frequency (f_c) =
$$\sqrt{\frac{1}{\text{R1R2C}^2}} \cdot \frac{1}{2\pi} = \sqrt{\frac{1}{\text{R1'R2'C}^2}} \cdot \frac{1}{2\pi}$$

- Passband gain (H_0) = (1 + R4/R3) (1 + R4'/R3')
- First stage Q = 1.31
- Second stage Q = 0.541
- Circuit shown uses closest 5% tolerance resistor values for a filter with a corner frequency of 1 kHz and a passband gain of 10

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Figure 32. Ohms to Volts Converter



$$V_{O} = \frac{1V}{R_{LADDER}} \times R_{X}$$

Where $R_{\mbox{\scriptsize LADDER}}$ is the resistance from switch S1 pole to pin 7 of the TL082CP.





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PACKAGING INFORMATION

Orderable Device	Status	Package Type	_		Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing			(2)		(3)		(4)	
TL082CM	ACTIVE	SOIC	D	8	95	TBD	CU SNPB	Level-1-235C-UNLIM	0 to 70	TL 082CM	Samples
TL082CM/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	TL 082CM	Samples
TL082CMX	ACTIVE	SOIC	D	8	2500	TBD	CU SNPB	Level-1-235C-UNLIM	0 to 70	TL 082CM	Samples
TL082CMX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	TL 082CM	Samples
TL082CP/NOPB	ACTIVE	PDIP	Р	8	40	Green (RoHS & no Sb/Br)	SN	Level-1-NA-UNLIM	0 to 70	TL082 CP	Samples
TL082CP/PB	ACTIVE	PDIP	Р	8	40	TBD	SNPB	Level-1-NA-UNLIM		TL082 CP	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based filp-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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⁽⁴⁾ Only one of markings shown within the brackets will appear on the physical device.



PACKAGE OPTION ADDENDUM

9-Feb-2013

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

	Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
I	TL082CMX	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
I	TL082CMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TL082CMX	SOIC	D	8	2500	349.0	337.0	45.0
TL082CMX/NOPB	SOIC	D	8	2500	349.0	337.0	45.0

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



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